

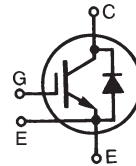
**1200V XPT™ IGBT  
GenX3™ w/ Diode**
**IXYN100N120B3H1**

$$V_{CES} = 1200V$$

$$I_{C110} = 76A$$

$$V_{CE(sat)} \leq 2.6V$$

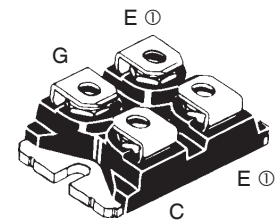
$$t_{fi(typ)} = 240ns$$

 Extreme Light Punch Through  
IGBT for 5-30 kHz Switching


Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $150^\circ C$	1200	V
$V_{CGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GE} = 1M\Omega$	1200	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$ (Chip Capability)	165	A
$I_{C110}$	$T_C = 110^\circ C$	76	A
$I_{F110}$	$T_C = 110^\circ C$	42	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	480	A
$I_A$	$T_C = 25^\circ C$	50	A
$E_{AS}$	$T_C = 25^\circ C$	1.2	J
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 150^\circ C$ , $R_G = 1\Omega$ Clamped Inductive Load	$I_{CM} = 200$ @ $V_{CE} \leq V_{CES}$	A
$P_C$	$T_C = 25^\circ C$	690	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$V_{ISOL}$	50/60Hz $I_{ISOL} \leq 1mA$	$t = 1min$ $t = 1s$	2500 3000 V~ V~
$M_d$	Mounting Torque Terminal Connection Torque	1.5/13 1.3/11.5	Nm/lb.in. Nm/lb.in.
<b>Weight</b>		30	g

SOT-227B, miniBLOC

E153432



G = Gate, C = Collector, E = Emitter  
① either emitter terminal can be used as  
Main or Kelvin Emitter

**Features**

- Optimized for 5-30kHz Switching
- Square RBSOA
- 2500V~ Isolation Voltage
- Anti-Parallel Ultra Fast Diode
- Positive Thermal Coefficient of  $V_{ce(sat)}$
- Avalanche Rated
- High Current Handling Capability
- International Standard Package

**Advantages**

- High Power Density
- Low Gate Drive Requirement

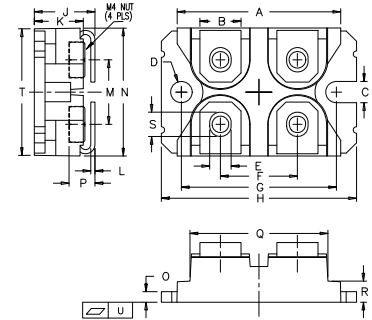
**Applications**

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu A$ , $V_{GE} = 0V$	1200		V
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.0		V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 125^\circ C$			50 $\mu A$ 2.75 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 100A$ , $V_{GE} = 15V$ , Note 1 $T_J = 150^\circ C$		2.20 2.76	2.60 V V

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 60\text{A}, V_{CE} = 10\text{V}$ , Note 1	30	52	S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		6000	pF
$C_{oes}$			367	pF
$C_{res}$			127	pF
$Q_{g(on)}$	$I_C = 100\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		250	nC
$Q_{ge}$			42	nC
$Q_{gc}$			96	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 100\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 1\Omega$ Note 2		30	ns
$t_{ri}$			90	ns
$E_{on}$			7.7	mJ
$t_{d(off)}$			153	ns
$t_{fi}$			240	ns
$E_{off}$		7.1	11.5	mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 150^\circ\text{C}</math></b> $I_C = 100\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 1\Omega$ Note 2		29	ns
$t_{ri}$			96	ns
$E_{on}$			11.4	mJ
$t_{d(off)}$			190	ns
$t_{fi}$			260	ns
$E_{off}$		10.1	mJ	
$R_{thJC}$			0.18	$^\circ\text{C/W}$
$R_{thCS}$		0.05		$^\circ\text{C/W}$

### SOT-227B miniBLOC (IXYN)



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

### Reverse Diode (FRED)

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_F$	$I_F = 60\text{A}, V_{GE} = 0\text{V}$ , Note 1 $T_J = 125^\circ\text{C}$		1.9	2.7 V
$I_{RM}$	$I_F = 60\text{A}, V_{GE} = 0\text{V}, T_J = 125^\circ\text{C}$ $-di_F/dt = 700\text{A}/\mu\text{s}, V_R = 600\text{V}$		41	A
$t_{rr}$			420	ns
$R_{thJC}$				0.42 $^\circ\text{C/W}$

#### Notes:

1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Switching times & energy losses may increase for higher  $V_{CE}$  (clamp),  $T_J$  or  $R_G$ .

### PRELIMINARY TECHNICAL INFORMATION

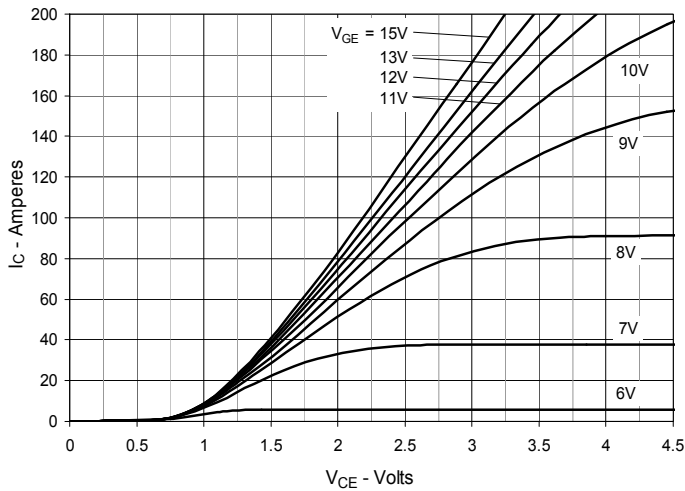
The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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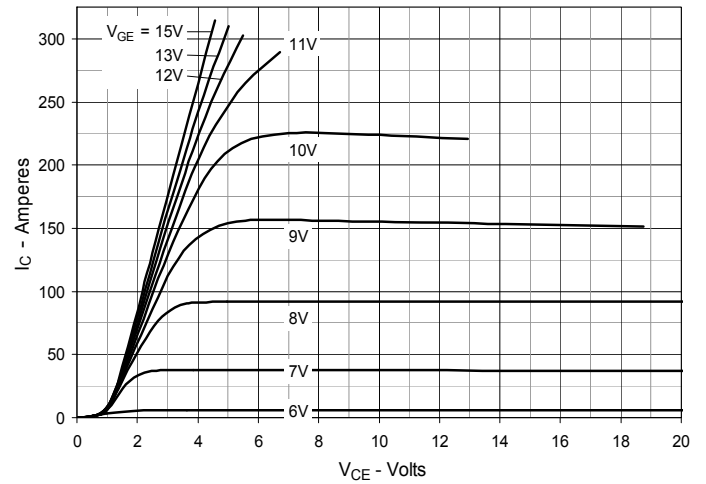
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

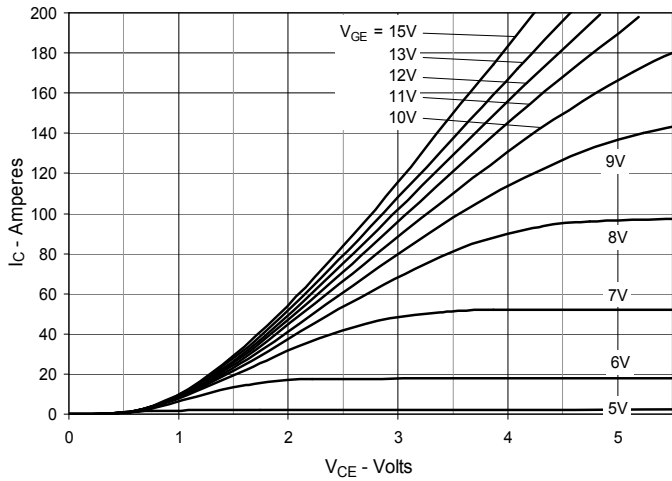
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



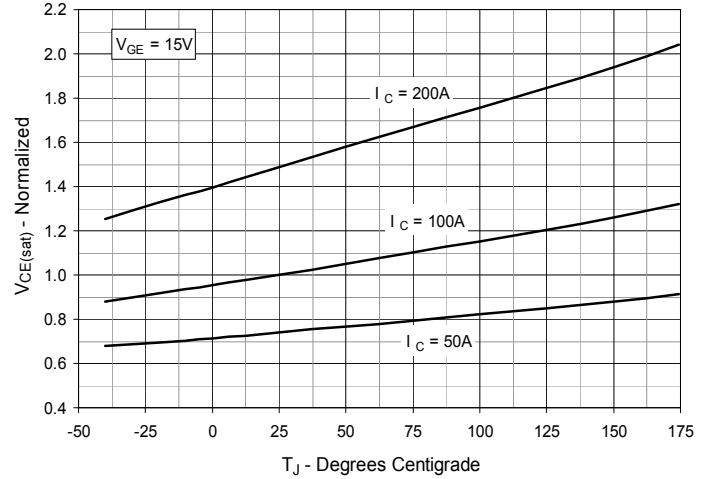
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



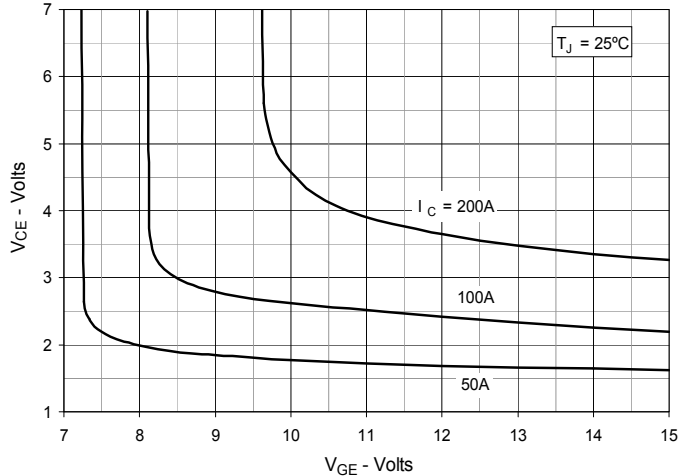
**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$**



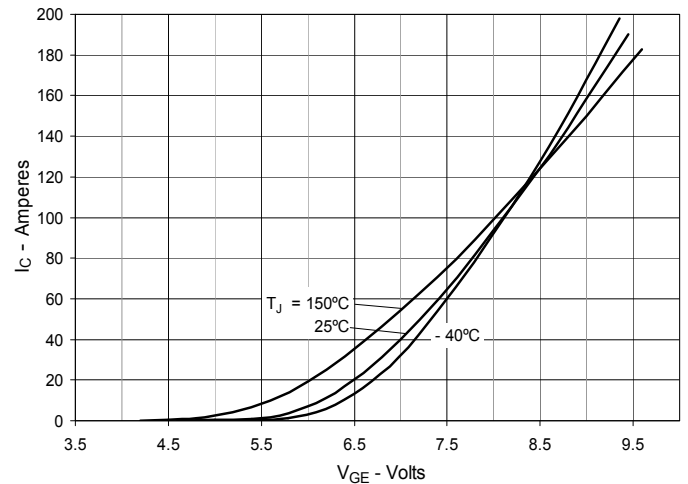
**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**



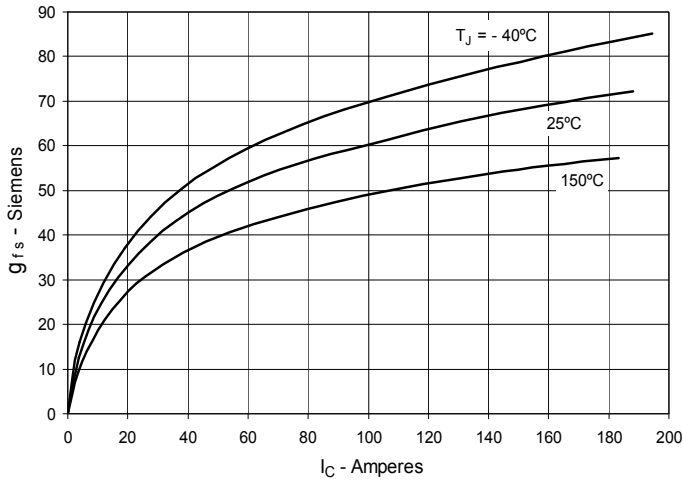
**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**



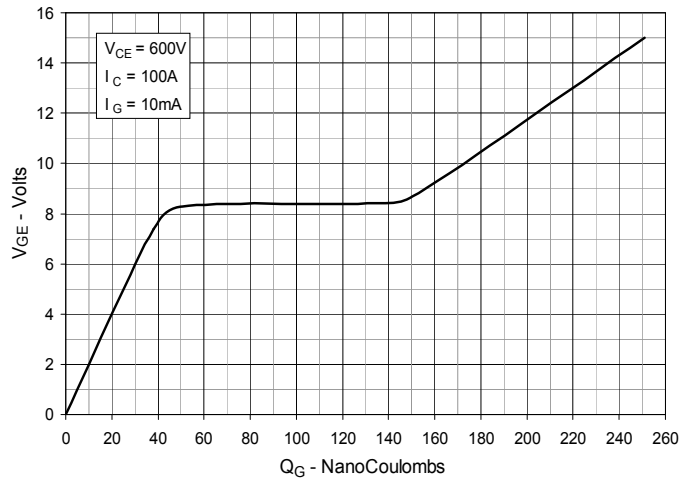
**Fig. 6. Input Admittance**



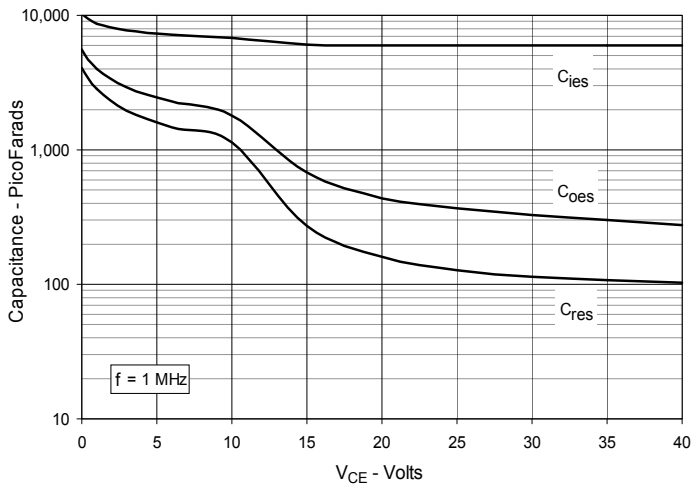
**Fig. 7. Transconductance**



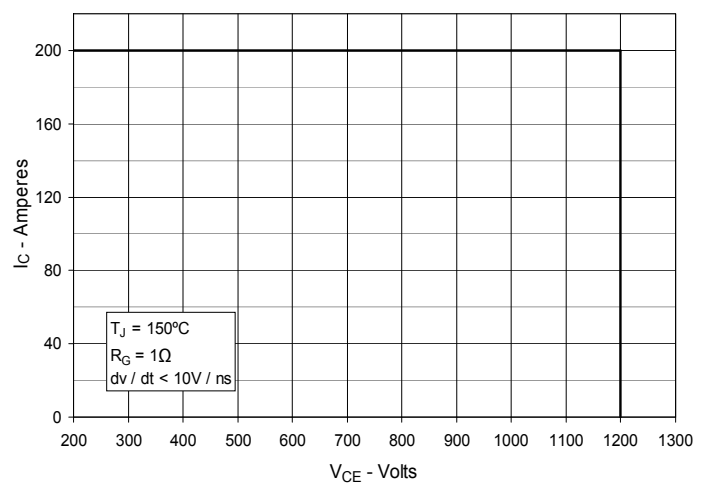
**Fig. 8. Gate Charge**



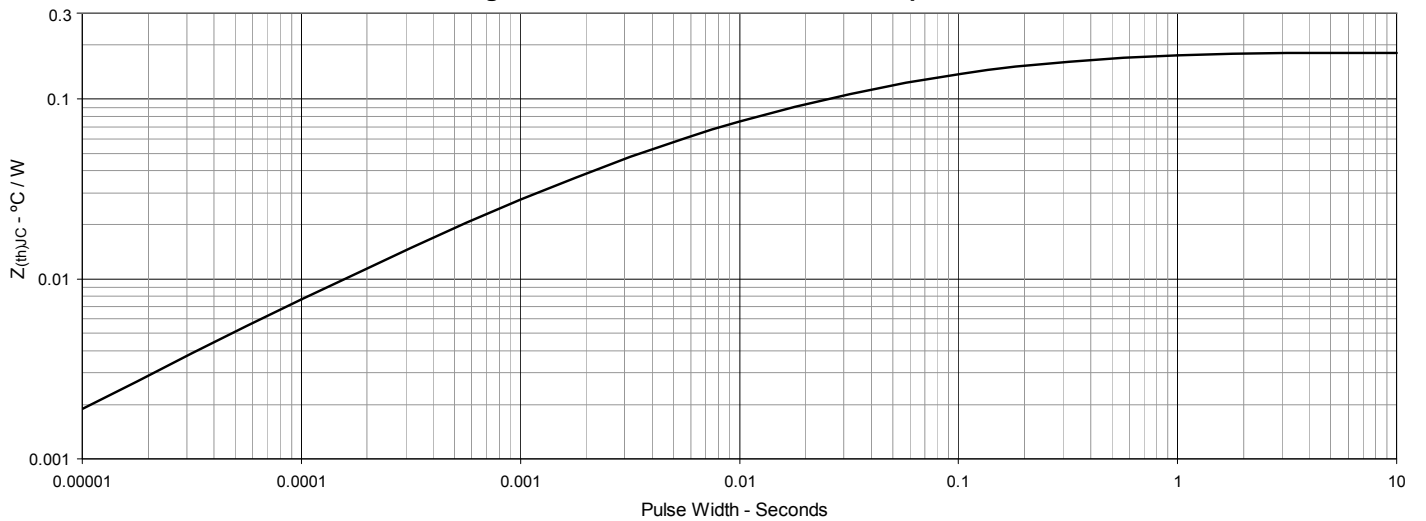
**Fig. 9. Capacitance**



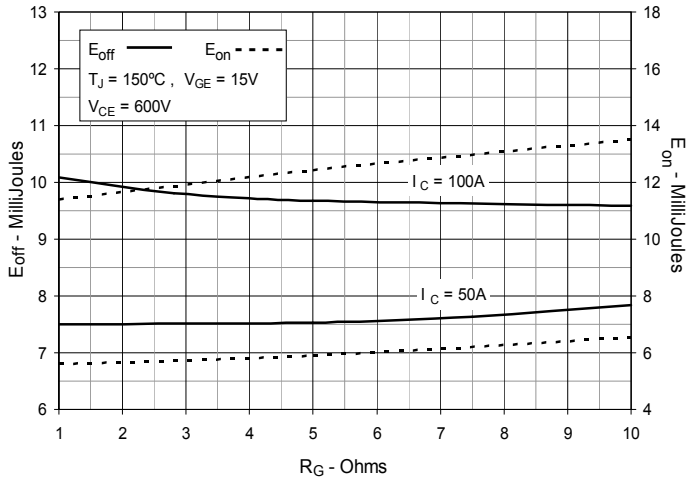
**Fig. 10. Reverse-Bias Safe Operating Area**



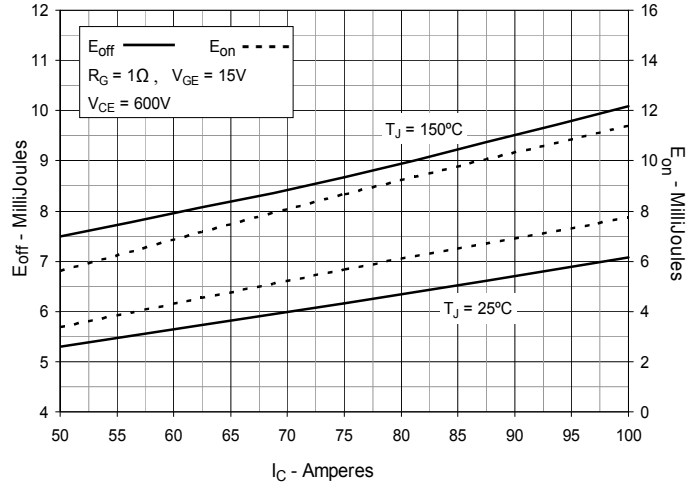
**Fig. 11. Maximum Transient Thermal Impedance**



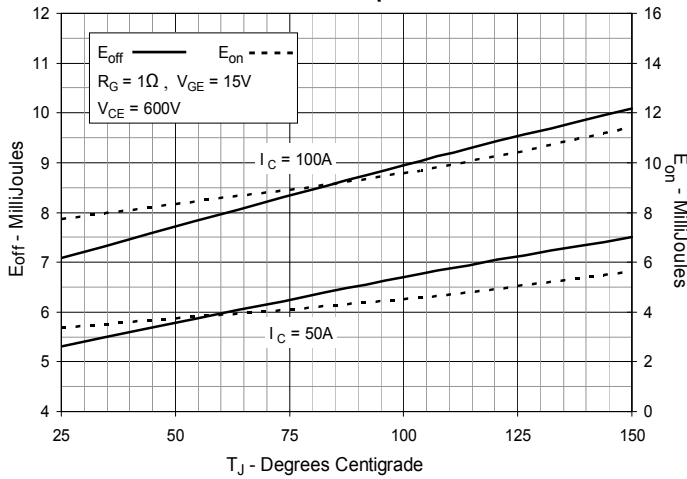
**Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance**



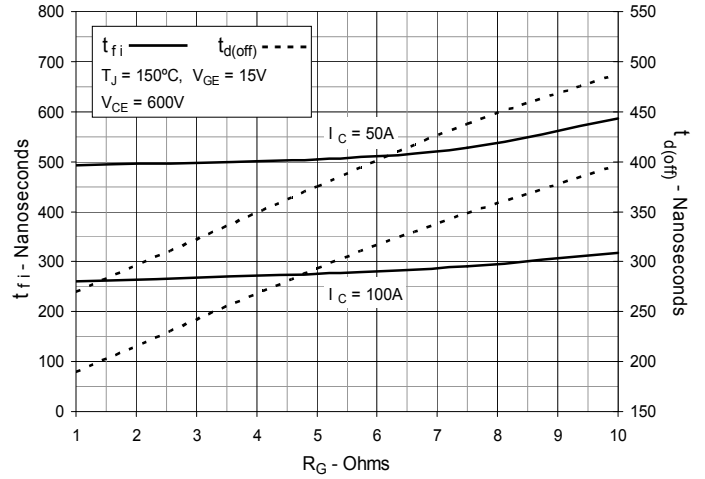
**Fig. 13. Inductive Switching Energy Loss vs. Collector Current**



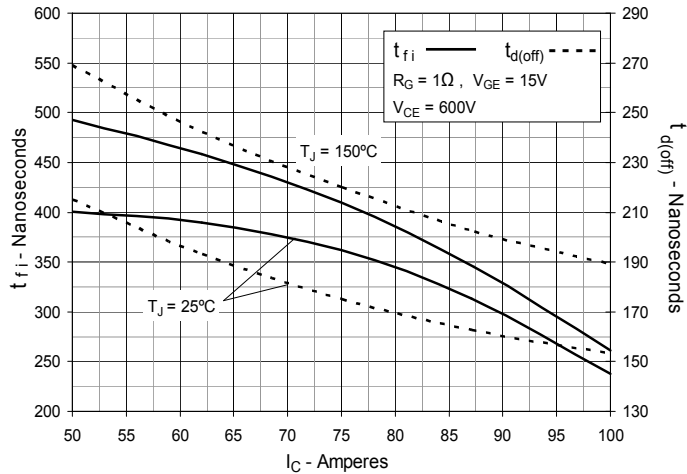
**Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature**



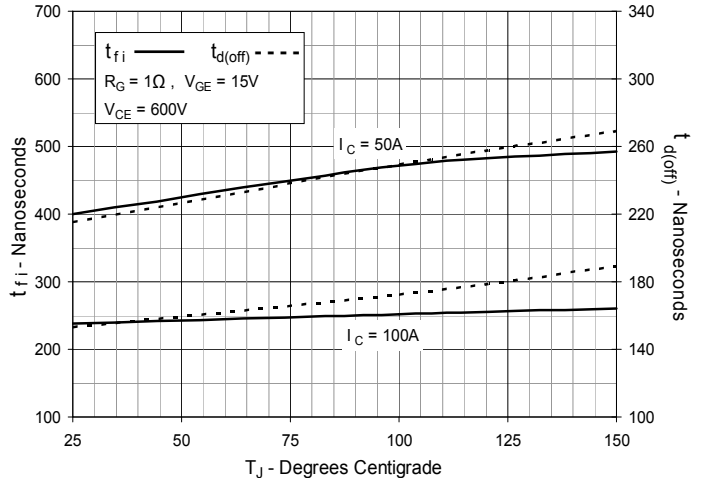
**Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance**

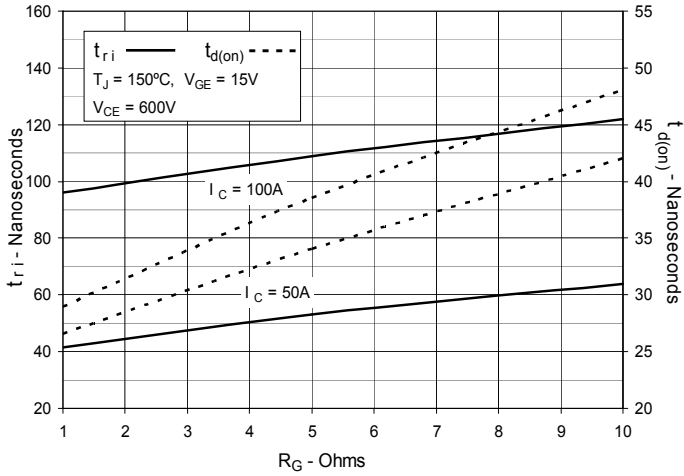
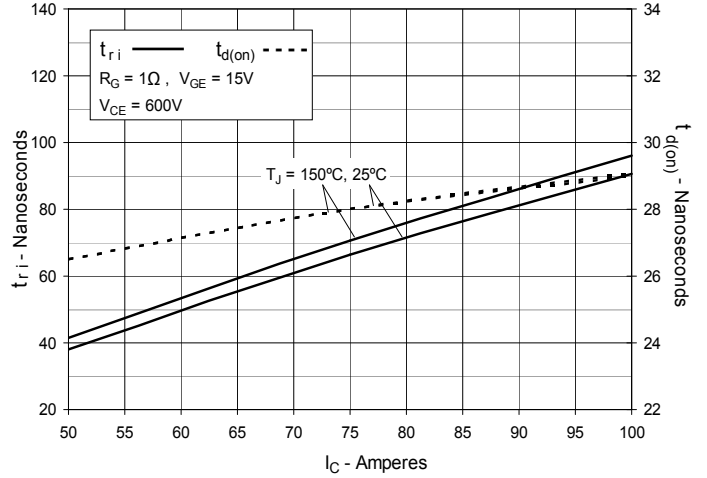
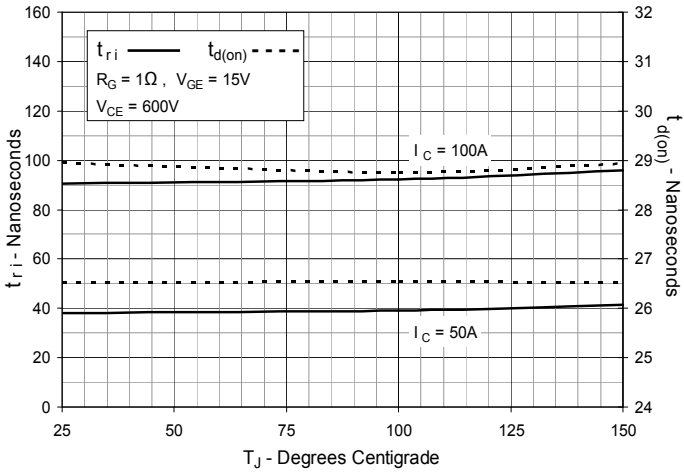


**Fig. 16. Inductive Turn-off Switching Times vs. Collector Current**

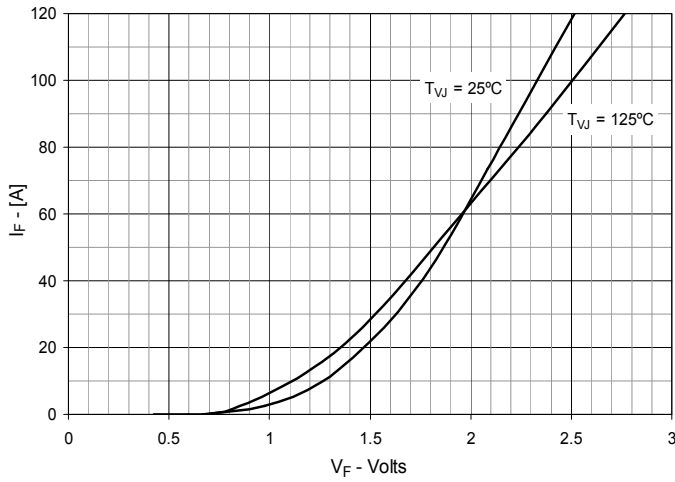


**Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature**

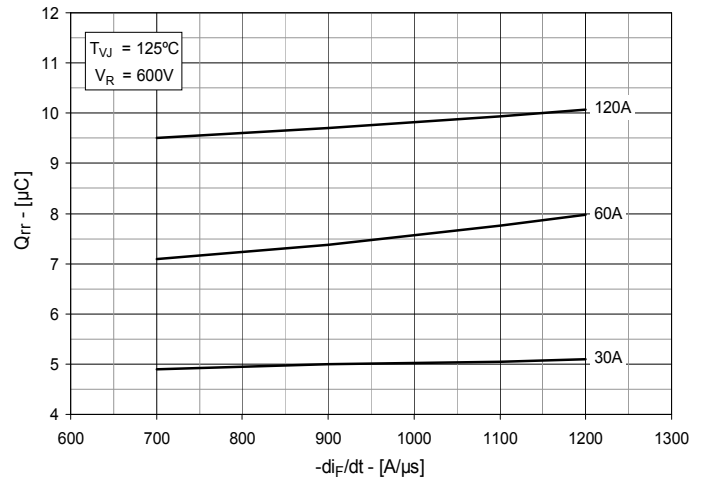


**Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance**

**Fig. 19. Inductive Turn-on Switching Times vs. Collector Current**

**Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature**


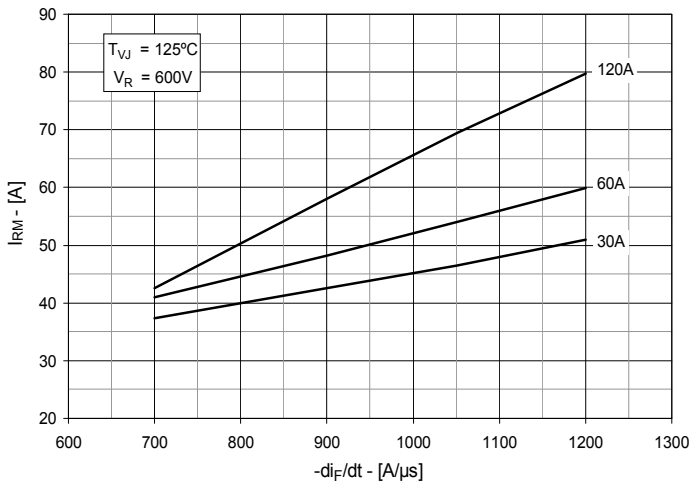
**Fig. 21. Typ. Forward Characteristics**



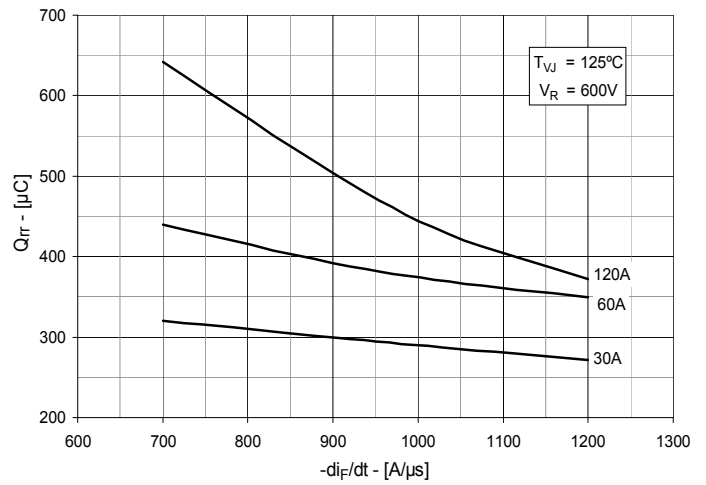
**Fig. 22. Typ. Reverse Recovery Charge  $Q_{rr}$  vs.  $-di_F/dt$**



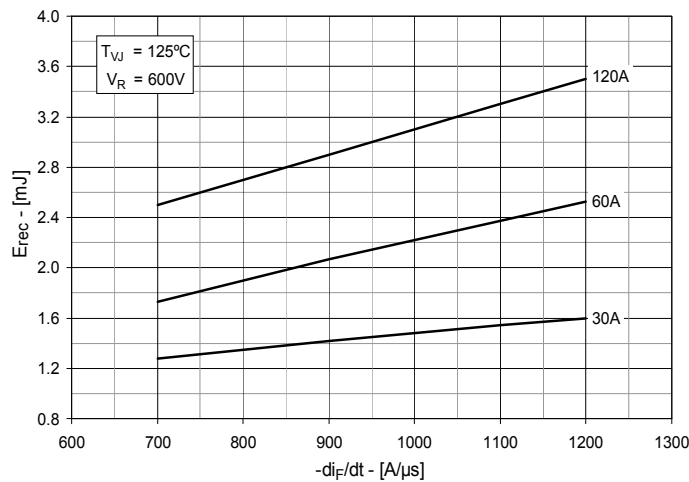
**Fig. 23. Typ. Peak Reverse Current  $I_{RM}$  vs.  $-di_F/dt$**



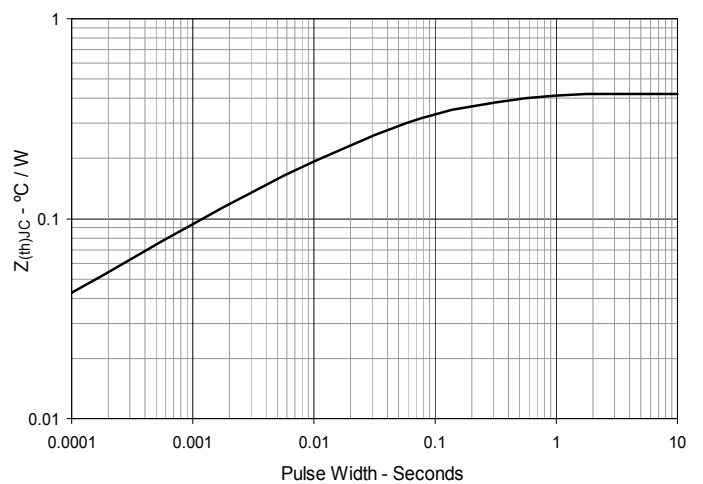
**Fig. 24. Typ. Recovery Time  $t_{rr}$  vs.  $-di_F/dt$**



**Fig. 25. Typ. Recovery Energy  $E_{rec}$  vs.  $-di_F/dt$**



**Fig. 26. Maximum Transient Thermal Impedance**





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